

IN THE SPECIFICATION:

Please amend the Title of the Invention section on Page 1 to read as follows:

~~{Document Name}~~ DESCRIPTION

~~{TITLE OF THE INVENTION}~~ SEMICONDUCTOR SUBSTRATE,
SEMICONDUCTOR DEVICE, AND MANUFACTURING METHOD FOR AND
~~PROCESS FOR PRODUCING~~ SEMICONDUCTOR SUBSTRATE

Please add the following heading and paragraph on Page 1 after the Title of the Invention, but before the subheading of Technical Art to read as follows:

CROSS REFERENCE TO RELATED APPLICATION

This application is a U.S. nationalization of International Application PCT/JP2004/014603, filed October 4, 2004, which claims the benefit of priority from Japanese Patent Application No. 2003-352692, filed October 10, 2003.

Please add the following heading on Page 1 before the subheading of Technical Art to read as follows:

BACKGROUND OF THE INVENTION

Please amend the subheading on Page 1 at line 5 to read as follows:

~~{TECHNICAL ART}~~ 1. Field of the Invention

Please amend the subheading on Page 1 at line 16 to read as follows:

~~[TECHNOLOGICAL BACKGROUND]~~ **2. Description of the Related Art**

Please amend Paragraph [0005] on Page 2 to read as follows:

[0005]As described above, there is a problem that a reduction in thickness of the SOI layer and the BOX layer would make it difficult to electrically well divide the SOI layer, so that the originally intended high-integration CMOSLSI cannot be manufactured.

~~[Patent Document 1]~~ ~~Japanese Unexamined Patent Application Publication No. Hei 9-161477~~

Please amend the subheadings before Paragraph [0006] and after Paragraph [0006] but before Paragraph [0007] on Page 2 to read as follows:

~~[DISCLOSURE OF THE INVENTION]~~

~~[PROBLEMS TO BE SOLVED BY THE INVENTION]~~ **SUMMARY OF THE INVENTION**

[0006]It is an object of the present invention to provide a novel semiconductor substrate, semiconductor device, and manufacturing method for the semiconductor substrate, which enables easy formation of a high-integration CMOSLSI based on inter-element isolation and sufficient reduction in the thickness of the SOI layer and the BOX layer, thereby preventing the short channel effect.

~~[MEANS TO SOLVE THE PROBLEMS]~~

Please amend line 25, on Page 4 to read as follows:

~~[ADVANTAGEOUS EFFECT OF THE INVENTION]~~

Please the subheading before Paragraph [0014] on Page 5 to read as follows:

~~[BRIEF DESCRIPTION OF THE DRAWINGS]~~ BRIEF DESCRIPTION OF THE
DRAWINGS

Please amend Paragraph [0014] on Page 5 to read as follows:

[0014] The nature, principle, and utility of the invention will become more
apparent from the following detailed description when read in conjunction with the
accompanying drawings in which like parts are designated by identical reference
numbers, in which:

Please amend the heading on Page 8, line 5, to read as follows:

~~[DESCRIPTION OF THE PREFERRED EMBODIMENTS]~~ DESCRIPTION OF
THE PREFERRED EMBODIMENTS